

## MAINTENANCE MANUAL

### 25-50 MHz RF ASSEMBLY 19D416478G1 - G4

### AND

### MIXER/IF/NOISE BLANKER BOARD 19D416562G1 - G4, 19D432681G1 - 4

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### DESCRIPTION

The RF Assembly uses two tuned helical resonators and four L-C tuned circuits to provide front end selectivity.

The Mixer/IF/Noise Blanker board (MIF/NB) uses the RF input from the RF Assembly and the mixer injection frequency from the oscillator/multiplier board to generate the IF frequency. The noise blanker eliminates undesirable noise interference in the received audio.

#### NOTE

The 19D416562 and 19D432681 Mixer/IF/Noise Blanker Boards are directly interchangeable. Earlier models used the 19D416562 board which is no longer in production. The Schematic Diagram is valid for both boards. Separate Parts Lists are provided.

### CIRCUIT ANALYSIS

#### RF ASSEMBLY

##### ANTENNA INPUT A301A/A301B

An RF signal is applied from the antenna input circuit (L551) of the noise blanker section of the MIF/NB board to A301-J1. The antenna input circuit provides an AC ground between vehicle ground and receiver A-. Resistor R1 prevents a static charge from building up on the vehicle antenna. The output of A301 is coupled through two high-Q helical resonators (L301, C301 and L302, C302) to the RF amplifier. The coils are tuned to the incoming frequency by C301 and C302. Lamp DS1 protects the RF amplifier stage against an excessive RF input.

#### RF AMPLIFIER A302

RF Amplifier Q1 is a Field-Effect Transistor (FET). Q1 operates as a grounded gate amplifier, with the RF input applied to the "source" terminal. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through four L-C tuned circuits (L1-C7, L2-C8, L3-C9 and L4-C10) to the mixer. The four tuned circuits and the two helical resonators provide the receiver front end selectivity.

#### MIXER/IF/NOISE BLANKER

##### MIXER & CRYSTAL FILTER

The mixer uses a FET (Q501) as the active device. The FET mixer provides a high input impedance, high power gain, and an output relatively free of harmonics (low in intermodulation products).

In the mixer stage, RF from the RF amplifier stage is coupled through tuned circuit L501 and C502 which matches the RF output to the gate of mixer Q501. Injection voltage from the multiplier-selectivity stages is inductively coupled through L502 to the source of the mixer. The mixer IF output signal is coupled from the drain of Q501 through a tuned circuit (L504 and C511) to the first FET noise blanker gate Q502. The IF signal is then coupled through a tuned circuit (L506 and C517) to the second FET noise blanker gate Q503.

During the presence of impulse noise from the antenna, the noise blanker circuit (U551) provides a positive pulse to the gates of Q502 and Q503 which attenuates the IF signal during the noise pulse period (see Noise Blanker description for details). This eliminates undesirable noise interference in the received audio without degrading receiver performance.

The mixer IF output signal is then coupled to the input of the four-pole monolithic crystal filter. The highly selective crystal filter (FL501 and FL502) provides the first portion of the receiver IF Selectivity. The output of the crystal filter is coupled through impedance-matching network Z502 (L520 and C501) to IF Amplifier Q520.

Service Note: Variable capacitor C521 does not require adjustment when performing normal alignment. If the four-pole monolithic crystal filter is replaced, then adjustment of C521 is necessary for optimum IF response.

#### IF AMPLIFIER

IF amplifier Q520 is a dual-gate FET. The crystal filter output is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing on Gate 2 and the drain load determines the gain of the stage. The amplifier provides approximately 20 dB of IF gain. The output of Q520 is coupled through a network (L521 and C528) that matches the amplifier output to the next IF stage. The output of the MIF/NB board is applied through feed-through capacitor C305 to the next IF stage or to the MIF switch when a dual front end is used.

Supply voltage for the RF amplifier and MIF/NB board is supplied through feed-through capacitor C306.

#### NOISE BLANKER

An RF signal and noise pulse from the antenna (J551) fed simultaneously to the Noise Blanker 1st RF Amplifier and the RF Assembly (A302) RF Amplifier. The signal and noise is transformer coupled through L551 to the 1st RF amplifier Q551 (dual-gate FET). The input signal is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing of Gate 2 and the drain load determines the gain of the stage. The signal is then coupled through tuned circuits L552/C558 and L553/C560 to the 2nd RF amplifier Q552, which is also a dual-gate FET. The combined gain of Q551 and Q552 is approximately 50 dB.

The amplified signal is coupled through tuned circuit L554/C564 to pulse detector/amplifier/switch IC (U551). IC (U551) is

a custom hybrid integrated circuit which contains a pulse detector, pulse amplifier, pulse amplifier/switch, intermodulation detector and a blanker disable switch. The IC functions as a pulse detector and processing circuit for the noise blanker. Regulated 10 VDC, which powers U551, is applied through pin 3. The associated capacitors (C571, C572 and C574) provide emitter decoupling for various stages of the IC.

#### Pulse Detector

The impulse noise from the RF amplifier is applied to pin 6 of U551 through tuned circuit L554/C564 to the pulse detector. Bias for the detector is established by R563, R564 and CR551. Diode CR551 is normally conducting, thus biasing the pulse detector. A positive pulse applied to the pulse detector causes it to conduct heavily. The output of the detector is a negative going pulse that is relatively free of any RF components. The pulse detector metering point (Blanker Meter) connects from pin 2 of U551 thru P553 to J605 on the next IF stage (J2305 on MIF switch when a DFE is used) and serves as a convenient measuring point when performing alignment.

#### Pulse Amplifier and Noise Blanker Disable Switch

The negative pulse output from the pulse detector turns the pulse amplifier on, producing a positive output pulse. The threshold point of the pulse amplifier and the RF gain of the 1st and 2nd RF amplifier stages (Q551 and Q552) in the noise blanker circuit prevent noise blanking due to any low-level inherent receiver noise.

A noise blanker disable switch provides a means for manually disabling the noise blanker circuits. Connecting pin 4 of U551 to A- turns the disable switch on, which in turn inhibits the pulse amplifier. The blanker disable function is also provided at pin 5 of the system plug (P904) for external control.

#### Pulse Amplifier/Switch

The positive output pulse from the pulse amplifier is fed to the pulse amplifier/switch. This circuit functions as a constant width pulse generator whose output is a positive 6 Volt pulse with a duration of 2 microseconds. This pulse is applied from pin 11 of U551 to the noise blanker gates (Q502 and Q503).

Noise blanker gates Q502 and Q503 are turned ON (conducting) during the presence of the noise blanking pulse. These gates present a low impedance RF path to A- for the pulse duration (approximately 3 microseconds), providing approximately 60 dB attenuation of the IF signal and the impulse noise present. As the noise signal from the antenna is applied to the noise blanker circuits, the RF signal is also applied to

the receiver RF input. The inherent delay presented to the received RF signal and the impulse noise by the helical resonators in the receiver RF assembly (L301 and L302) and the four tuned circuits (L1/C7 through L4/C10) allows the noise blanking pulse to turn on the blanking gates. This attenuates the received signal just prior to the arrival of the impulse noise.

#### Intermodulation (IM) Detector

The output of the pulse amplifier is also applied to the IM detector. The IM detector does not respond to noise pulses appearing at its input because of the cir-

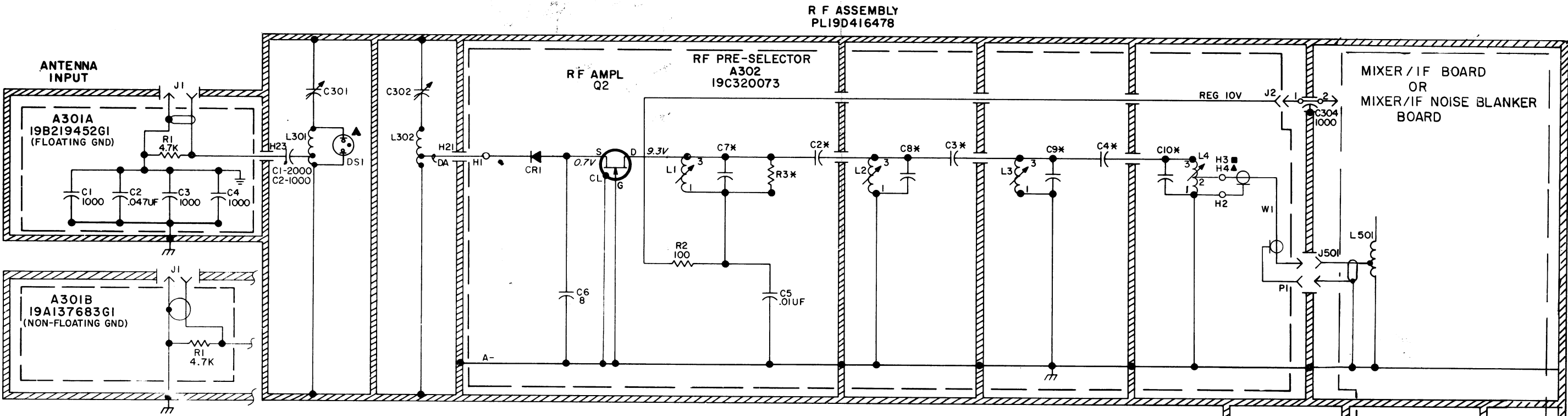
cuit design utilized, but the detector is activated during the presence of a sinusoidal signal. This sinusoidal signal is the beat frequency difference of two signals present in the noise blanker channel.

A resultant AGC voltage (approximately +3 VDC) is developed through the integrating action of C573 and is applied from pin 13 of U551 to the 2nd RF amplifier (Q552) of the noise blanker circuit. This action sufficiently reduces the gain of the noise blanker RF stage (Q552) so that receiver performance is not degraded by blanking pulses which would create receiver intermodulation close to the receiver operating frequency.

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION  
WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.







* COMPONENT VALUE TABLE				
COMP DESIG	LL	L	M	H
RF FREQ	25-30MHZ	30-36MHZ	36-42 MHZ	42-50MHZ
IF FREQ	11.2 MHZ	9.4 MHZ	11.2 MHZ	9.4 MHZ
C2	1.0	.75	.68	.82
C3	1.0	.75	.68	.82
C4	1.0	.75	.68	.82
C7	51	39	30	18
C8	51	39	30	18
C9	51	39	30	18
C10	56	39	30	18
R3			24K	6.2K

MID BAND		
* COMPONENT VALUE TABLE		
SPLIT	ML LOW	MH HIGH
RF FREQ	66-78MHZ	77-88MHZ
IF FREQ	11.2 MHZ	11.2 MHZ
C2	.47	.39
C3	.56	.47
C4	1.0	.82
C7	15	10
C8	18	13
C9	18	13
C10	18	13
R3	6.8K	6.8K

RF ASSEMBLY	REV	RF PRE-SELECTOR	REV	ANTENNA INPUT	REV	FREQ (MHZ)
	LTR		LTR		LTR	
19D416478G1	C	19C320073G1	C	19B219452GI	-	25-30 (LL)
19D416478G2	C	19C320073G2	F	19B219452GI	-	30-36 (L)
19D416478G3	B	19C320073G3	E	19B219452GI	-	36-42 (M)
19D416478G4	B	19C320073G4	C	19B219452GI	-	42-50 (H)
19D416478G8	-	19C320073G8	-	19B219452GI	-	66-78 (ML)
19D416478G9	-	19C320073G9	-	19B219452GI	-	77-88 (MH)
19D416478G10	-	19C320073G1	C	19B219452GI	-	25-30 (LL)
19D416478G11	-	19C320073G2	F	19A137683GI	-	30-36 (L)
19D416478G12	-	19C320073G3	E	19A137683GI	-	36-42 (M)
19D416478G13	-	19C320073G4	C	19A137683GI	-	42-50 (H)
19D416478G14	-	19C320073G8	-	19A137683GI	-	66-78 (ML)
19D416478G15	-	19C320073G9	-	19A137683GI	-	77-88 (MH)

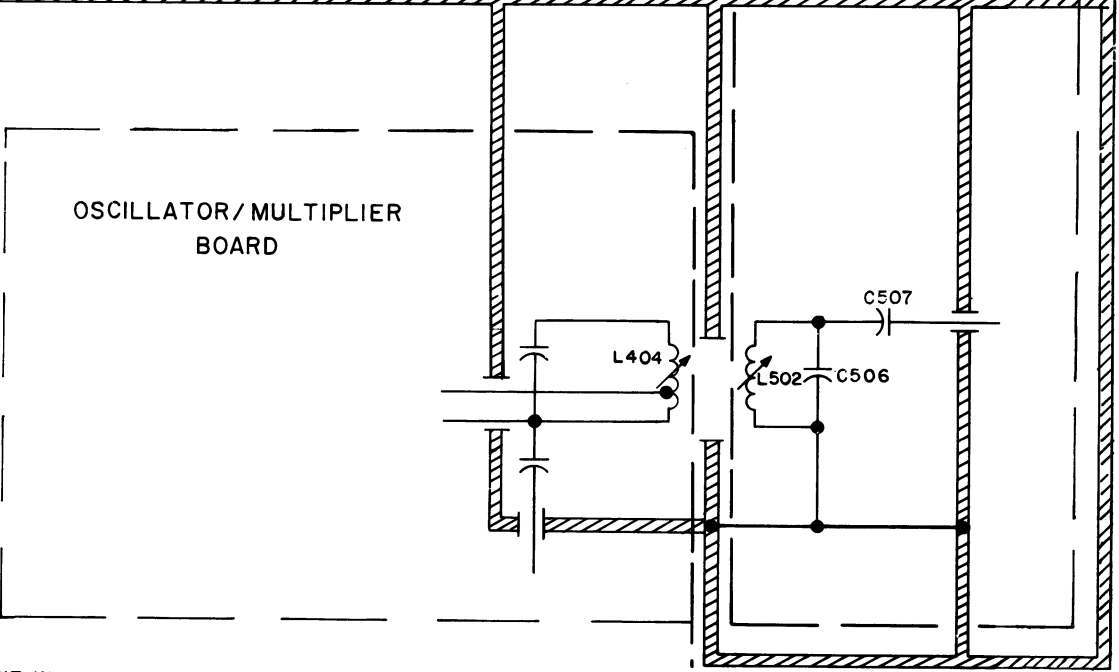
**VOLTAGE READINGS**  
VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3A11 OR A 20,000 OHM-PER-VOLT METER.

⚡ INDICATES A-  
⏏ INDICATES VEHICLE GROUND

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICO FARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

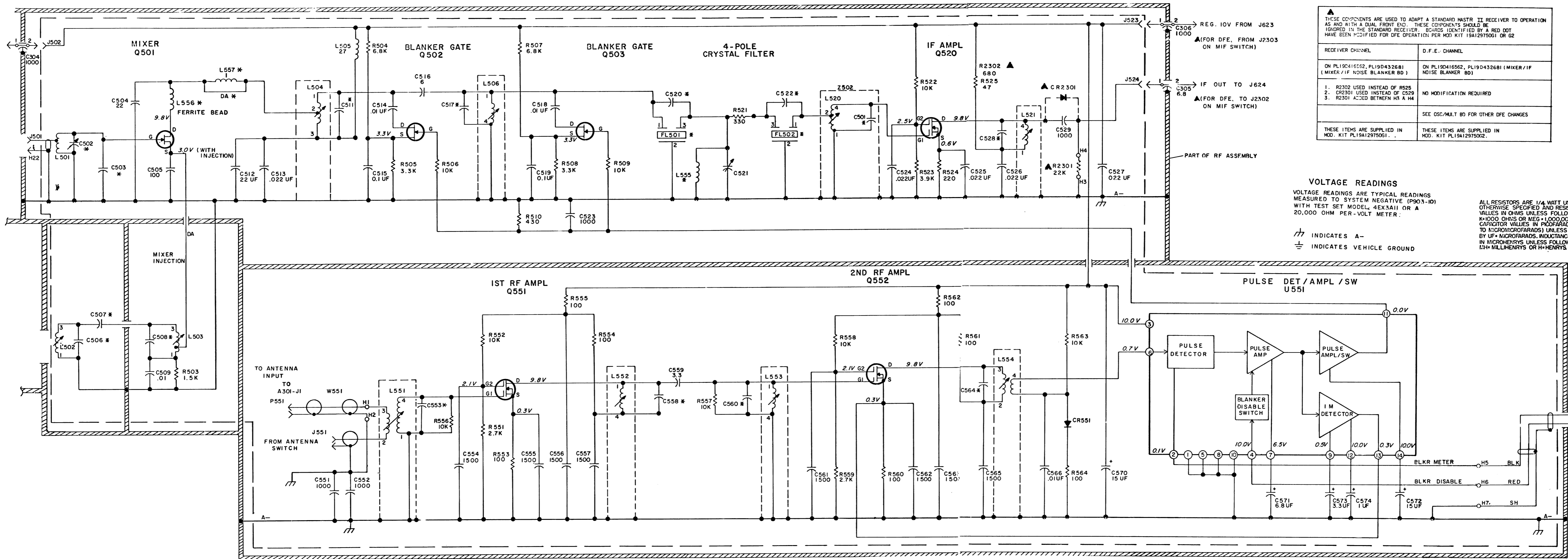
▲ NOT PRESENT IN M.B.  
■ NOT PRESENT IN L.B.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.



**SCHEMATIC DIAGRAM**

25—50 MHz RF AMPLIFIER ASSEMBLY



THESE COMPONENTS ARE USED TO ADAPT A STANDARD MASTR II RECEIVER TO OPERATION AS AND WITH A DUAL FRONT END. THESE COMPONENTS SHOULD BE IGNORED IN THE STANDARD RECEIVER. BOARDS IDENTIFIED BY A RED DOT HAVE BEEN MODIFIED FOR DFE OPERATION PER MOD KIT 19A129750G1 OR G2

RECEIVER CHANNEL	D.F.E. CHANNEL
ON PL19D416562, PL19D4326B1 (MIXER/IF NOISE BLANKER BD)	ON PL19D416562, PL19D4326B1 (MIXER/IF NOISE BLANKER BD)
1. R2302 USED INSTEAD OF R525 2. CR2301 USED INSTEAD OF C529 3. R2301 ADDED BETWEEN H3 & H4	NO MODIFICATION REQUIRED
SEE OSC/MULT BD FOR OTHER DFE CHANGES	
THESE ITEMS ARE SUPPLIED IN MOD. KIT 19A129750G1.	THESE ITEMS ARE SUPPLIED IN MOD. KIT 19A129750G2.

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3A11 OR A 20,000 OHM PER-VOLT METER.

INDICATES A-  
INDICATES VEHICLE GROUND

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MILLIHENRYS UNLESS FOLLOWED BY H=HENRYS.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

	REV	FREQ	IF
MIXER/IF NOISE BLANKER	LETTER	RANGE (MHZ)	FREQ (MHZ)
19D416562G1	H	25-30 (LL)	11.2
19D416562G2	G	30-36 (L)	9.4
19D416562G3	H	36-42 (M)	11.2
19D416562G4	G	42-50 (H)	9.4
19D432681G1		25-30 (LL)	11.2
19D432681G2		30-36 (L)	9.4
19D432681G3		36-42 (M)	11.2
19D432681G4		42-50 (H)	9.4

COMP DESIG	LL	L	M	H
RF FREQ	25-30MHZ	30-36MHZ	36-42 MHZ	42-50MHZ
IF FREQ	11.2 MHZ	9.4 MHZ	11.2 MHZ	9.4 MHZ
C502	8-50	8-50	2-20	2-20
C503	56	39	27	15
C506	27	24	15	12
C507	1.0	.82	.68	.56
C508	27	22	15	12
C511	47	82	47	82
C517	68	100	68	100
C520	.47	.56	.47	.56
C522	.47	.56	.47	.56
C528	330	360	330	360
C553	68	47	68	47
C558	68	47	68	47
C560	68	47	68	47
C564	68	47	68	47
L555	15	18	15	18
R3		30K	15K	6.2K
FL501	FL501LL	FL501L	FL501M	FL501H
FL502	FL502LL	FL502L	FL502M	FL502H
L556	FERR BEAD	FERR BEAD	NOT USED	NOT USED
L557	DA	DA	I	I

SCHEMATIC DIAGRAM  
25-50 MHz MIXER/IF/NOISE BLANKER  
Issue 6

PARTS LIST		
LBI4992H		
25-50 MHz		
RF ASSEMBLY 19D416478G1-G4, G10-13		
AND		
MIXER/IF/NOISE BLANKER		
19D416562G1-G4		

SYMBOL	GE PART NO.	DESCRIPTION
A301A	19A116655P19	RF ASSEMBLY 19D416478G1 25-30 MHz (LL) FLOATING GRD. 19D416478G2 30-36 MHz (L) FLOATING GRD. 19D416478G3 36-42 MHz (M) FLOATING GRD. 19D416478G4 42-50 MHz (H) FLOATING GRD. 19D416478G10 25-30 MHz (LL) NON FLOATING GRD. 19D416478G11 30-36 MHz (L) NON FLOATING GRD. 19D416478G12 36-42 MHz (M) NON FLOATING GRD. 19D416478G13 42-50 MHz (H) NON FLOATING GRD.
		COMPONENT BOARD 19B219452G1
		----- CAPACITORS -----
		C1 Ceramic disc: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		C2 Polyester: 0.047 uF ±10%, 50 VDCW.
		C3 and C4 Ceramic disc: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		----- JACKS AND RECEPTACLES -----
		J1 Connector, receptacle; 500 VDCW maximum; sim to NTF-1058.
		----- RESISTORS -----
		R1 Composition: 4.7K ohms ±5%, 1/4 w.
A301B	19A700106P79	ANTENNA PLATE ASSEMBLY 19A137683G1
		----- JACKS AND RECEPTACLES -----
		J1 Jack, phono: coaxial.
		----- RESISTORS -----
		R1 Composition: 4.7K ohms ±5%, 1/4 w.
A302	19A700013P13	COMPONENT BOARD A302LL 19C320073G1 25-30 MHz (LL) A302L 19C320073G2 30-36 MHz (L) A302M 19C320073G3 36-42 MHz (M) A302H 19C320073G4 42-50 MHz (H)
		----- CAPACITORS -----
		C2LL* Phenolic: 1.00 pF ±5%, 500 VDCW. In REV A and earlier:
		C2L* Phenolic: 1.2 pF ±10%, 500 VDCW.
		C2L* Phenolic: 0.75 pF ±5%, 500 VDCW.
		In REV B and earlier:
		C2M* Phenolic: 1.0 pF ±5%, 500 VDCW.
		In REV C and earlier:
		C2H* Phenolic: 0.82 pF ±5%, 500 VDCW.
		In REV A and earlier:
C3LL*	19A700013P13	Phenolic: 1.00 pF ±5%, 500 VDCW.
		In REV A and earlier:
		C3H* Phenolic: 0.82 pF ±5%, 500 VDCW.
		In REV B and earlier:
		C3L* Phenolic: 0.75 pF ±5%, 500 VDCW.
		In REV B and earlier:
		C4M* Phenolic: 1.0 pF ±5%, 500 VDCW.
		In REV C and earlier:
		C4H* Phenolic: 0.82 pF ±5%, 500 VDCW.
		In REV A and earlier:
C4L*	5491601P118	Phenolic: 0.75 pF ±5%, 500 VDCW.
		In REV B and earlier:
		C4M* Phenolic: 1.0 pF ±5%, 500 VDCW.
		In REV C and earlier:
		C4H* Phenolic: 0.82 pF ±5%, 500 VDCW.
		In REV A and earlier:
		C5 Phenolic: 1.0 pF ±5%, 500 VDCW.
		Polyester: 0.01 uF ±10%, 50 VDCW.
		C6 Ceramic disc: 8 pF ±10%, 500 VDCW; temp. coef -80 PPM.
		C7LL Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
C7L	5496219P256	Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7L Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8LL 5496219P256 Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9LL 5496219P256 Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
C9M	5496219P250	Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10LL 5496219P257 Ceramic disc: 56 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		----- DIODES AND RECTIFIERS -----
		CR1 Silicon, fast recovery; sim to Hewlett Packard 5082-2811.
		----- JACKS AND RECEPTACLES -----
		J2 Contact, electrical.

SYMBOL	GE PART NO.	DESCRIPTION
C3L*	5491601P118	Phenolic: 0.75 pF ±5%, 500 VDCW. In REV B and earlier:
		5491601P120 Phenolic: 1.0 pF ±5%, 500 VDCW.
		C3M* 19A700013P11 Phenolic: 0.68 pF ±5%, 500 VDCW. In REV C and earlier:
		5491601P119 Phenolic: 0.82 pF ±5%, 500 VDCW.
		C3H* 19A700013P12 Phenolic: 0.82 pF ±5%, 500 VDCW. In REV A and earlier:
		5491601P120 Phenolic: 1.0 pF ±5%, 500 VDCW.
		C4LL* 19A700013P13 Phenolic: 1.00 pF ±5%, 500 VDCW. In REV A and earlier:
		5491601P122 Phenolic: 1.2 pF ±5%, 500 VDCW.
		C4L* 5491601P118 Phenolic: 0.75 pF ±5%, 500 VDCW. In REV B and earlier:
		5491601P120 Phenolic: 1.0 pF ±5%, 500 VDCW.
C4M*	19A700013P11	Phenolic: 0.68 pF ±5%, 500 VDCW. In REV C and earlier:
		5491601P119 Phenolic: 0.82 pF ±5%, 500 VDCW.
		C4H* 19A700013P12 Phenolic: 0.82 pF ±5%, 500 VDCW. In REV A and earlier:
		5491601P120 Phenolic: 1.0 pF ±5%, 500 VDCW.
		C5 19A700005P7 Polyester: 0.01 uF ±10%, 50 VDCW.
		C6 19A116656P8K8 Ceramic disc: 8 pF ±10%, 500 VDCW; temp. coef -80 PPM.
		C7LL 5496219P256 Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C7H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
C8LL	5496219P256	Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C8H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9LL 5496219P256 Ceramic disc: 51 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9M 5496219P250 Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C9H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10LL 5496219P257 Ceramic disc: 56 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10L 5496219P253 Ceramic disc: 39 pF ±5%, 500 VDCW, temp. coef -80 PPM.
C10M	5496219P250	Ceramic disc: 30 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		C10H 5496219P245 Ceramic disc: 18 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		----- DIODES AND RECTIFIERS -----
		CR1 In REV A and earlier:
		Phenolic: 1.0 pF ±5%, 500 VDCW.
		In REV A and earlier:
		Phenolic: 1.0 pF ±5%, 500 VDCW.
		In REV A and earlier:
		Phenolic: 1.2 pF ±5%, 500 VDCW.
		In REV A and earlier:
C3LL*	19A700013P13	Phenolic: 1.00 pF ±5%, 500 VDCW.
		In REV A and earlier:
		Phenolic: 1.2 pF ±5%, 500 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
L1* thru L3*	19C307170P306	----- INDUCTORS ----- Coil, RF; variable, wire size No. 20 AWG; sim. to Paul Smith Co. Sample No. 092574-D8-3. In 19C320073G1 REV A and earlier: In 19C320073G2 REV B and earlier: In 19C320073G3 REV C and earlier: In 19C320073G4 REV A and earlier:
		19B219419G2 Coil. Includes:
		5491798P5 Tuning slug.
		L4* 19C307170P308 Coil, RF; variable, wire size No. 20 AWG; sim. to Paul Smith Co. Sample No. 071774-DG-7. In 19C320073G1 REV A and earlier: In 19C320073G2 REV B and earlier: In 19C320073G3 REV C and earlier: In 19C320073G4 REV A and earlier:
		19B219419G1 Coil. Includes:
		5491798P5 Tuning slug.
		----- PLUGS -----
		P1 (Part of W1).
		----- TRANSISTORS -----
		Q2 N Type, field effect; sim to Type 2N4416.
RESISTORS	19A700106P39	Composition: 100 ohms ±5%, 1/4 w.
		R3L* 3R152P303J Composition: 30K ohms ±5%, 1/4 w. Deleted by REV B. Added to G2 by REV D. Deleted in G2 by REV F.
		R3M* 3R152P243J Composition: 24K ohms ±5%, 1/4 w. Added by REV C.
		3R152P153J Composition: 15K ohms ±5%, 1/4 w. Deleted by REV B.
		R3H 3R152P622J Composition: 6200 ohms ±5%, 1/4 w.
		----- CABLES -----
		W1 Cable, RF: approx 4 inches long. (Includes P1).
		----- CAPACITORS -----
		C301 (Part of L301).
		C302 (Part of L302).
19B209488P2	19B209488P2	Ceramic: 1000 pF -10+100%, 500 VDCW; sim to Allen Bradley Style FASD.
		C305 Ceramic: 6.8 pF ±20%, 500 VDCW; sim to Allen Bradley Style FASD.
		C306 Ceramic: 1000 pF -10+100%, 500 VDCW; sim to Allen Bradley Style FASD.
INDUCTORS	19A116656P2J28	Ceramic disc: 22 pF ±5%, 500 VDCW, temp. coef -80 PPM.
		L301LL and L301L 19B219455G1 Coil. Includes:
		C1* 5494481P13 Ceramic disc: 2900 pF ±20%, 1000 VDCW; sim. to Type JF Discap.
		5494481P11 In REV B and earlier:
		Ceramic disc: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		19B209067P1 Lamp, glow: 0.7 mA; sim to GE NE2ET.
		19B219455G3 Coil. Includes:
		5494481P11 Ceramic disc: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
		DS1 19B209067P1 Lamp, glow: 0.7 mA; sim to GE NE2ET.
		19B219455G2 Coil. Includes:
L302LL and L302L	19B219455G2	Coil. Includes:
		19B219455G4 Coil. Includes:
		L302M and L302H

SYMBOL	GE PART NO.	DESCRIPTION
		----- MISCELLANEOUS -----
	19B201074P305	Tap screw, Phillips PQ2DRIV: No. 6-32 x 5/16. (Secures A301 and A302).
	19B219451P1	Cover.
		MIXER/IF/NOISE BLANKER BOARD 19D416562G1 25-30 MHz (LL) 19D416562G2 30-36 MHz (L) 19D416562G3 36-42 MHz (M) 19D416562G4 42-50 MHz (H)
		----- CAPACITORS -----
C501LL		(Part of Z502LL).
C501L		(Part of Z502L).
C501M		(Part of Z502M).
C501H		(Part of Z502H).
C502LL and C502L	5490446P1	Variable, ceramic: approx. 8-50 pF, 350 VDCW, temp. coef -750 PPM; sim to Erie Style 557-36.
C502M and C502H	19A700012P2	Variable, ceramic: 2.5 to 20 pF 200 VDCW, temp coef -250 -700 PPM; sim to Panasonic ECK1ZW20X32.
C503LL	5490008P21	Silver mica: 56 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503L	5490008P17	Silver mica: 39 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503M	5490008P13	Silver mica: 27 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503H	5490008P8	Silver mica: 15 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C504	19A116656P2J20	Ceramic disc: 22 pF ±5%, 500 VDCW, temp coef 0 PPM.
C505	5490008P27	Silver mica: 100 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C506LL	19A116656P2J28	Ceramic disc: 27 pF ±5%, 500 VDCW, temp coef -80 PPM.
C506L	19A116656P2J28	Ceramic disc: 22 pF ±5%, 500 VDCW, temp coef -80 PPM.
C506M	19A116656P15J8	Ceramic disc: 15 pF ±5%, 500 VDCW, temp coef -80 PPM.
C506H	19A116656P12J8	Ceramic disc: 12 pF ±5%, 500 VDCW; temp. coef -80 PPM.
C507LL	19A700013P13	Phenolic: 1.00 pF ±5%, 500 VDCW.
C507L	19A700013P12	Phenolic: 0.82 pF ±5%, 500 VDCW.
C507M	19A700013P11	Phenolic: 0.68 pF ±5%, 500 VDCW.
C507H	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C508LL	19A116656P2J28	Ceramic disc: 27 pF ±5%, 500 VDCW, temp coef -80 PPM.
C508L	19A116656P2J28	Ceramic disc: 22 pF ±5%, 500 VDCW, temp coef -80 PPM.
C508M	19A116656P15J8	Ceramic disc: 15 pF ±5%, 500 VDCW, temp coef -80 PPM.
C508H	19A116656P12J8	Ceramic disc: 12 pF ±5%, 500 VDCW; temp. coef -80 PPM.
C509	19A700005P7	Polyester: 0.01 uF ±10%, 50 VDCW.
C511LL	5490008P119	Silver mica: 47 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C511L	5490008P125	Silver mica: 82 pF ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C511M	5490008P119	Silver mica: 47 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C511H	5490008P125	Silver mica: 82 pF ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C512	5496267P10	Tantalum: 22 uF ±20%, 15 VDCW; sim to Sprague Type 150D.
C513	19A700005P9	Polyester: 0.022 uF ±10%, 50 VDCW.
C514	19A700005P7	Polyester: 0.01 uF ±10%, 50 VDCW.
C515	19A116080P107	Polyester: 0.1 uF ±10%, 50 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
	4035306P23	Insulator, fiber. (Used with J501).
	4035306P59	Insulator, fiber. (Used with L501).
		DUAL FRONT END MOD KIT 19A129750G1 RECEIVER 19A129750G2 DFE
C2301*	19A116656P8J0	----- CAPACITORS ----- Ceramic disc: 8 pF +0.5 pF, 500 VDCW; temp coef 0 PPM. Deleted by REV B.
CR2301	19A116925P1	----- DIODES AND RECTIFIERS ----- Silicon, pin: 35 volt Reverse Breakdown, 400 mW.
		----- RESISTORS -----
R2301	19A700106P95	Composition: 22K ohms ±5%, 1/4 w.
R2302	19A700106P59	Composition: 680 ohms ±5%, 1/4 w.
R2303	3R152P911J	Composition: 910 ohms ±5%, 1/4 w.
		----- CABLES -----
W2301	19B219999G2	Cable, RF: approx 1 foot long. Includes: (1) 5496078P2 connector.

PARTS LIST		
		MIXER/1F/NOISE BLANKER BOARD 19D432681G1 25-30 MHz (LL) 19D432681G2 30-36 MHz (L) 19D432681G3 36-42 MHz (M) 19D432681G4 42-50 MHz (H) ISSUE 2
SYMBOL	GE PART NO.	DESCRIPTION
		----- CAPACITORS -----
C501LL		(Part of Z502LL).
C501L		(Part of Z502L).
C501M		(Part of Z502M).
C501H		(Part of Z502H).
C502LL and C502L	5490446P1	Variable, ceramic: approx. 8-50 pF, 350 VDCW, temp. coef -750 PPM; sim. to Erie Style 557-36.
C502M and C502H	19A700012P2	Variable, ceramic: 2.5 to 20 pF 200 VDCW, temp coef -250 -700 PPM; sim to Panasonic ECX1ZW20X32.
C503LL	5490008P21	Silver mica: 56 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503L	5490008P17	Silver mica: 39 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503M	5490008P13	Silver mica: 27 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C503H	5490008P8	Silver mica: 15 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C504	19A701624P16	Ceramic, disc: 22 pF ±5%, 500 VDCW, temp coef 0 PPM ±30.
C505	5490008P27	Silver mica: 100 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C506LL	19A701624P118	Ceramic, disc: 27 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C506L	19A701624P116	Ceramic, disc: 22 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C506M	19A701624P112	Ceramic, disc: 15 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C506H	19A701624P110	Ceramic, disc: 12 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C507LL	19A700013P13	Phenolic: 1.00 pF ±5%, 500 VDCW.
C507L	19A700013P12	Phenolic: 0.82 pF ±5%, 500 VDCW.
C507M	19A700013P11	Phenolic: 0.68 pF ±5%, 500 VDCW.
C507H	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C508LL	19A701624P118	Ceramic, disc: 27 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C508L	19A701624P116	Ceramic, disc: 22 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C508M	19A701624P112	Ceramic, disc: 15 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C508H	19A701624P110	Ceramic, disc: 12 pF ±5%, 500 VDCW, temp coef N80 PPM ±30.
C509	T644ACP310K	Polyester: 0.01 uF ±10%, 50 VDCW.
C511LL	5490008P119	Silver mica: 47 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C511L	5490008P125	Silver mica: 82 pF ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C511M	5490008P119	Silver mica: 47 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C511H	5490008P125	Silver mica: 82 pF ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C512	315A6047P226N	Tantalum: 0.47 uF ±20%, 35 VDCW.
C513	19A143477P17	Polyester: 0.22 uF ±20%, 50 VDCW.
C514	T644ACP310K	Polyester: 0.01 uF ±10%, 50 VDCW.
C515	T644ACP410K	Polyester: 0.1 uF ±10%, 50 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
C516	19A701624P4	Ceramic, disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM ±60.
C517LL	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C517L	5490008P127	Silver mica: 100 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C517M	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C517H	5490008P127	Silver mica: 100 pF ±10%, 500 VDCW, sim. to Electro Motive Type DM-15.
C518	T644ACP310K	Polyester: 0.01 uF ±10%, 50 VDCW.
C519	T644ACP410K	Polyester: 0.1 uF ±10%, 50 VDCW.
C520LL	19A700013P9	Phenolic: 0.47 pF ±5%, 500 VDCW.
C520L	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C520M	19A700013P9	Phenolic: 0.47 pF ±5%, 500 VDCW.
C520H	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C521	19A700012P2	Variable, ceramic: 2.5 to 20 pF 200 VDCW, temp coef -250 -700 PPM; sim to Panasonic ECX1ZW20X32.
C522LL	19A700013P9	Phenolic: 0.47 pF ±5%, 500 VDCW.
C522L	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C522M	19A700013P9	Phenolic: 0.47 pF ±5%, 500 VDCW.
C522H	19A700013P10	Phenolic: 0.56 pF ±5%, 500 VDCW.
C523	19A116192P13	Ceramic: 1000 pF ±10%, 50 VDCW; sim to Erie 8121-A050-W5R-102K.
C524 thru C527	19A143477P17	Polyester: 0.22 uF ±20%, 50 VDCW.
C528LL	5490008P39	Silver mica: 330 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C528L	5490008P40	Silver mica: 360 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C528M	5490008P39	Silver mica: 330 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C528H	5490008P40	Silver mica: 360 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C529	19A701602P19	Ceramic: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C551 and C552	19A701602P19	Ceramic: 1000 pF ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C553LL	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C553L	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C553M	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C553H	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C554 thru C557	19A116192P10	Ceramic: 1500 pF ±10%, 50 VDCW; sim to Erie 8121-A050-W5R-152K.
C558LL	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C558L	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C558M	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C558H	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C559	5491601P130	Phenolic: 3.6 pF ±5%, 500 VDCW.
C560LL	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C560L	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C560M	5490008P23	Silver mica: 68 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C560H	5490008P19	Silver mica: 47 pF ±5%, 500 VDCW, sim. to Electro Motive Type DM-15.

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	GE PART NO.	DESCRIPTION
C561 thru C563	19A116192P10	Ceramic: 1500 pF $\pm$ 10%, 50 VDCW; sim to Erie 8121-A050-WSR-152K.
C564LL	5490008P23	Silver mica: 68 pF $\pm$ 5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C564L	5490008P19	Silver mica: 47 pF $\pm$ 5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C564M	5490008P23	Silver mica: 68 pF $\pm$ 5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C564H	5490008P19	Silver mica: 47 pF $\pm$ 5%, 500 VDCW, sim. to Electro Motive Type DM-15.
C565	19A116192P10	Ceramic: 1500 pF $\pm$ 10%, 50 VDCW; sim to Erie 8121-A050-WSR-152K.
C566	T644ACP410K	Polyester: 0.1 uF $\pm$ 10%, 50 VDCW.
C570	19A143486P10	Tantalum: 15 uF $\pm$ 20%, 20 VDCW.
C571	19A143486P1	Tantalum: 6.8 uF $\pm$ 20%, 6 VDCW.
C572	19A143486P10	Tantalum: 15 uF $\pm$ 20%, 20 VDCW.
C573	19A143486P7	Tantalum: 3.3 uF $\pm$ 20%, 15 VDCW.
C574	315A6047P105U	Tantalum: 1 uF $\pm$ 20%, 35 VDCW.
- - - - - DIODES AND RECTIFIERS - - - - -		
CR551	19A115775P1	Silicon, fast recovery, 225 mA, 50 PIV.
- - - - - FILTERS - - - - -		
FL501LL	19B219573G3	Crystal, freq: Resonator A - 11,200.000 KHz; Resonator B - 11,196.024 KHz.
FL501L	19B219574G3	Crystal, freq: Resonator A - 9400.000 KHz, Resonator B - 9396.024 KHz.
FL501M	19B219573G3	Crystal, freq: Resonator A - 11,200.000 KHz; Resonator B - 11,196.024 KHz.
FL501H	19B219574G3	Crystal, freq: Resonator A - 9400.000 KHz, Resonator B - 9396.024 KHz.
FL502LL		(Part of FL501LL).
FL502L		(Part of FL501L).
FL502M		(Part of FL501M).
FL502H		(Part of FL501H).
- - - - - JACKS AND RECEPTACLES - - - - -		
J501	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.
J502	19A116975P1	Receptacle, wire spring.
J523 and J524	19A116975P1	Receptacle, wire spring.
J551	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.
- - - - - INDUCTORS - - - - -		
L501		(Part of printed board).
L502	19B219419G2	Coil. Includes: 5491798P5
L503	19B219419G4	Coil. Includes: 5491798P5
L504	19C320141G24	Coil. Includes: 5493185P12
L505	19A700024P30	Coil, RF: 27 uH $\pm$ 10%.
L506	19C320141G23	Coil. Includes: 5493185P9
L520LL		(Part of Z502LL).
L520L		(Part of Z502L).
L520M		(Part of Z502M).
L520H		(Part of Z502H).

SYMBOL	GE PART NO.	DESCRIPTION
L521	19C320141G6	Coil. Includes: 5493185P9
L551	19C320141G12	Coil. Includes: 5493185P9
L552 and L553	19C320141G7	Coil. Includes: 5493185P9
L554	19C320141G13	Coil. Includes: 5493185P9
L555LL	19B209420P27	Coil, RF: 15.0 uH $\pm$ 5%, 2.80 ohms DC res max; sim to Jeffers 1316-2J.
L555L	19B209420P28	Coil, RF: 18.0 uH $\pm$ 5%, 3.00 ohms DC res max; sim to Jeffers 1316-3S.
L555M	19B209420P27	Coil, RF: 15.0 uH $\pm$ 5%, 2.80 ohms DC res max; sim to Jeffers 1316-2J.
L555H	19B209420P28	Coil, RF: 18.0 uH $\pm$ 5%, 3.00 ohms DC res max; sim to Jeffers 1316-3S.
L556	19A700103P1	Torridal core.
L557	19A700024P13	Coil, RF: 1.0 uH $\pm$ 10%.
- - - - - PLUGS - - - - -		
P551		(Part of W551).
P553 and P554		(Part of W552).
- - - - - TRANSISTORS - - - - -		
Q501	19A116154P1	N Type, field effect.
Q502 and Q503	19A134137P6	N Type, field effect.
Q520	19A116818P1	N Channel, field effect.
Q551 and Q552	19A116818P1	N Channel, field effect.
- - - - - RESISTORS - - - - -		
R503	19A700106P67	Composition: 1.5K ohms $\pm$ 5%, 1/4 w.
R504	19A700106P83	Composition: 6.8K ohms $\pm$ 5%, 1/4 w.
R505	19A700106P75	Composition: 3.3K ohms $\pm$ 5%, 1/4 w.
R506	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R507	19A700106P83	Composition: 6.8K ohms $\pm$ 5%, 1/4 w.
R508	19A700106P75	Composition: 3.3K ohms $\pm$ 5%, 1/4 w.
R509	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R510	3R152P431J	Composition: 430 ohms $\pm$ 5%, 1/4 w.
R521	19A700106P51	Composition: 330 ohms $\pm$ 5%, 1/4 w.
R522	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R523	19A700106P77	Composition: 3.9K ohms $\pm$ 5%, 1/4 w.
R524	19A700106P47	Composition: 220 ohms $\pm$ 5%, 1/4 w.
R525	19A700106P31	Composition: 47 ohms $\pm$ 5%, 1/4 w.
R551	19A700106P73	Composition: 2.7K ohms $\pm$ 5%, 1/4 w.
R552	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R553 thru R555	19A700106P39	Composition: 100 ohms $\pm$ 5%, 1/4 w.
R556 thru R558	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R559	19A700106P73	Composition: 2.7K ohms $\pm$ 5%, 1/4 w.
R560 thru R562	19A700106P39	Composition: 100 ohms $\pm$ 5%, 1/4 w.
R563	19A700106P87	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R564	19A700106P39	Composition: 100 ohms $\pm$ 5%, 1/4 w.

SYMBOL	GE PART NO.	DESCRIPTION
U551	19D417378G2	- - - - - INTEGRATED CIRCUITS - - - - - Noise Blanker.
W551	19B232879G1	- - - - - CABLES - - - - - Cable, RF: approx 2-1/4 inches long; 350 VRMS, 500 VDC operating voltage.
W552	19B219764G3	Cable: 2 conductor with shield, approx 8-1/4 inches long.
Z502LL		- - - - - NETWORKS - - - - - COIL ASSEMBLY 19C320141G16
C501LL	19A700220P63	- - - - - CAPACITORS - - - - - Ceramic: 91 pF $\pm$ 5%, 100 VDCW; temp coef -30 PPM
L520LL	19C320141P26 19B209674P2	- - - - - INDUCTORS - - - - - Coil. Includes: Tuning slug.
Z502L		COIL ASSEMBLY 19C320141G27
C501L	19A700220P64	- - - - - CAPACITORS - - - - - Ceramic: 100 pF $\pm$ 10%, 100 VDCW, temp coef -30 PPM.
L520L	19C320141P26 19B209674P2	- - - - - INDUCTORS - - - - - Coil. Includes: Tuning slug.
Z502M		COIL ASSEMBLY 19C320141G16
C501M	19A700220P63	- - - - - CAPACITORS - - - - - Ceramic: 91 pF $\pm$ 5%, 100 VDCW; temp coef -30 PPM.
L520M	19C320141P26 19B209674P2	- - - - - INDUCTORS - - - - - Coil. Includes: Tuning slug.
Z502H		COIL ASSEMBLY 19C320141G27
C501H	19A700220P64	- - - - - CAPACITORS - - - - - Ceramic: 100 pF $\pm$ 10%, 100 VDCW, temp coef -30 PPM.
L520H	19C320141P26 19B209674P2	- - - - - INDUCTORS - - - - - Coil. Includes: Tuning slug.
	19B219470P2	- - - - - MISCELLANEOUS - - - - - Shield.
	19A129424G1	Can. (Used with L504, L506, L520, L521, L551-L554).
	4031594P1	Insulator. (Used with C521).
	4035306P23	Insulator, fiber. (Used with J501).
	4035306P59	Insulator, fiber. (Used with L501).

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A thru E - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. A thru D - Mixer/IF/Noise Blanker Board 19D416562G3, 4
- REV. A - RF Filter Board 19C320073G1-4  
The above revisions incorporated in initial shipment.
- REV. B - RF Filter Board 19C320073G2 & 3  
To improve receiver sensitivity. Deleted R3L and R3M.
- REV. C - RF Filter Board 19C320073G3  
To prevent oscillation. Added R3M.
- REV. B - RF Filter Board 19C320073G1, 4
- REV. C - RF Filter Board 19C320073G2
- REV. D - RF Filter Board 19C320073G3  
To improve receiver sensitivity. Changed C2, C3 and C4 and L1 thru L4.
- REV. F - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. E - Mixer/IF/Noise Blanker Board 19D416562G3, 4  
To improve blanker operation. Changed Q502 and Q503.
- REV. G - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. F - Mixer/IF/Noise Blanker Board 19D416562G3, 4  
To improve operation. Added L556.
- REV. A & B - RF Assembly 19D416478G1-4  
Incorporated in initial shipment.
- REV. C - RF Assembly 19D416478G1, 2  
To improve sensitivity in 25-30 MHz range. Changed C1 (part of L301).
- REV. D - RF Filter Board 19C320073G2  
To prevent oscillations in pre-selector board  
Added R3L.
- REV. G - Mixer/IF/Noise Blanker 19D416562G3, 4  
To prevent oscillations in mixer. Replace L556 with L557. Connected C504 to Q501D.
- REV. C - RF Filter Board 19C320073G1, G4
- REV. E - RF Filter Board 19C320073G2, G3  
To standardize components. Deleted Q1 and PWB 19C320072. Added Q2 and PWB 19C327760P1.
- REV. H - Mixer/IF/Noise Blanker 19D416562G1 & G3  
To improve operation in the 25-30 MHz and 36-42 MHz range. Changed C517.